


Course : Electronic device & circuits

: Summer Semester

Instructor : Dr. Shauyar Shafiq

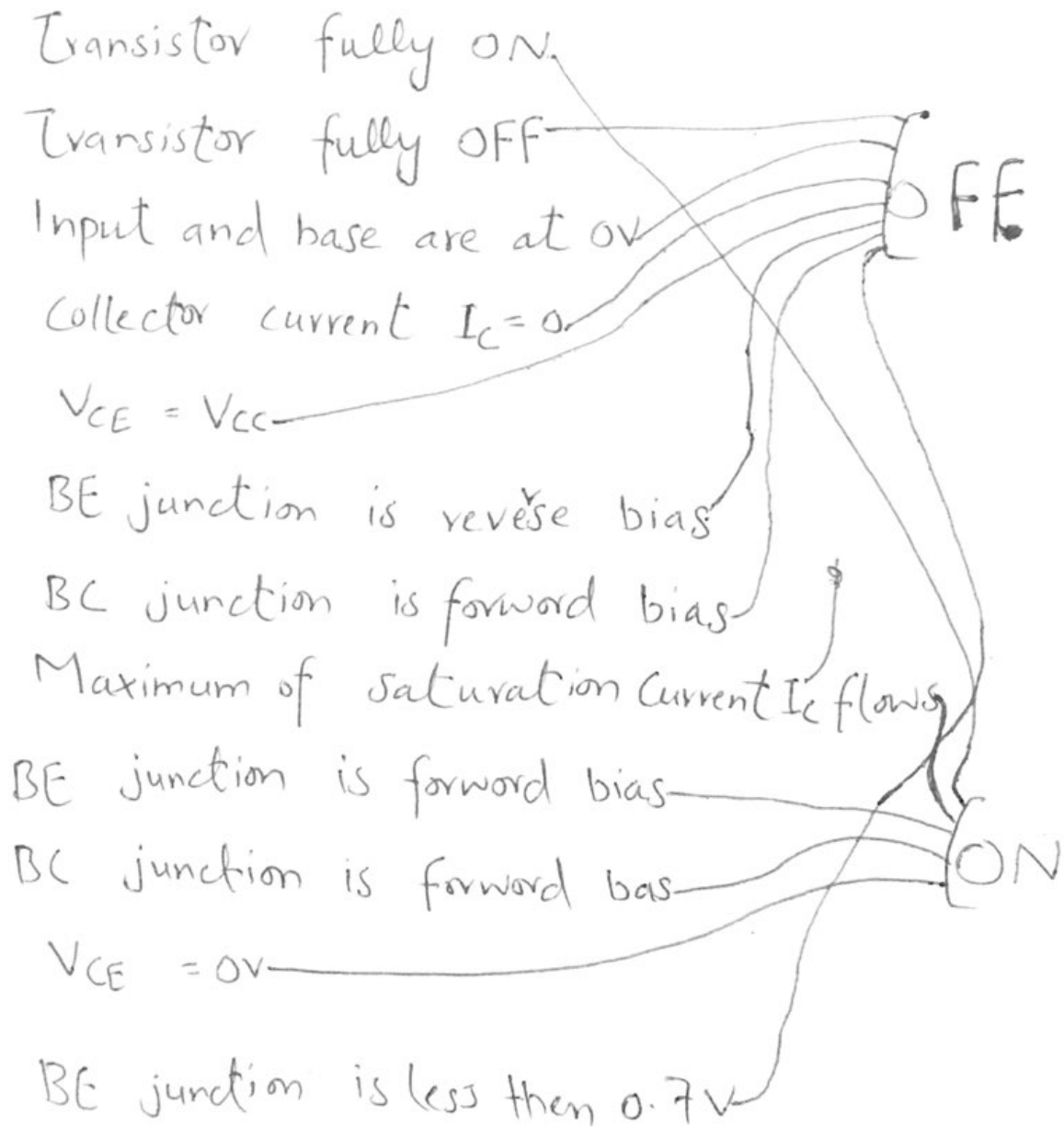
Name : Farhan Ali

ID : 14873

Signature : The signature is a stylized, cursive script. It begins with a large, sweeping flourish that curves upwards and then downwards. Below this flourish, the name 'Farhan' is written in a smaller, more legible cursive, and 'Ali' is written below that. A horizontal line is drawn under the name 'Farhan'.

f. Q4:-

→ For a Transistor to act a "switch"
You need to join each of the following
condition on the left "ON" or "OFF" state.

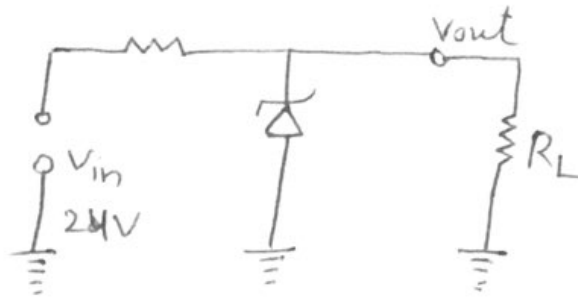


Q1:-

Part (a):-

Find the data sheet

Sol:-



from the data sheet 1N4747A

$$V_z = 15 \text{ V} \text{ @ } I_z = 12.5 \text{ mA} \text{ and } Z_z = 22 \Omega$$

$$I_{zK} = 0.25 \text{ mA}$$

(a) for I_{zK} :-

$$V_{out} = V_z - I_z Z_z$$

$$= 15 - (I_z - I_{zK}) Z_z$$

$$= 15 - (12.25 \text{ mA})(22 \Omega)$$

$$= 15 \text{ V} - (0.01225)(22)$$

$$= 15 \text{ V} - 0.2695$$

$$= 14.7305 \text{ V}$$

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Calculating Zener Max Current the maximum power dissipation is 1W

$$I_{ZM} = \frac{P_0(\text{max})}{V_Z} = \frac{1W}{15} = 0.066667A$$

$$I_{ZM} = 66.7mA$$

for I_{ZM} :

$$\begin{aligned} V_{out} &= V_Z + \Delta I Z_Z \\ &= 15V + \Delta I Z_Z \\ &= 15V + (I_{ZM} - I_Z) Z_Z \\ &= 15V + (54.2mA) (22\Omega) \\ &= 15V + (0.0542) (22) \\ &= 16.1924V \end{aligned}$$

Part B:-

Calculate value of R for Max Zener Current that occurs when there is no load

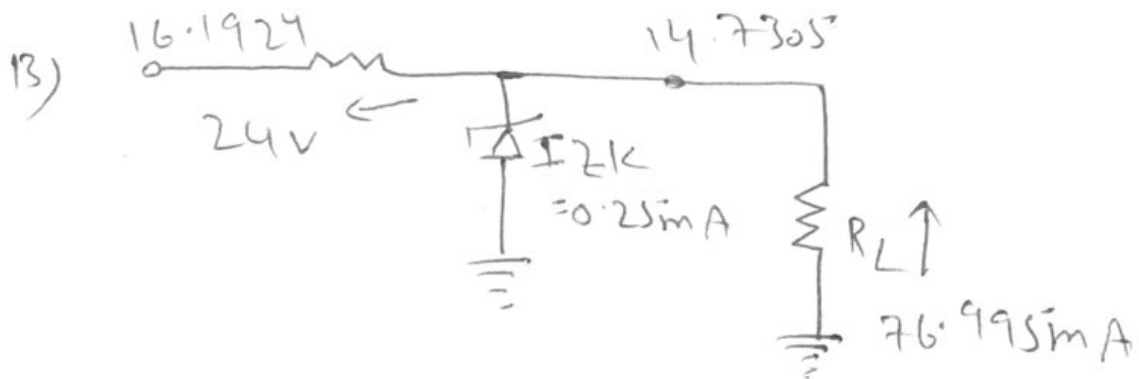
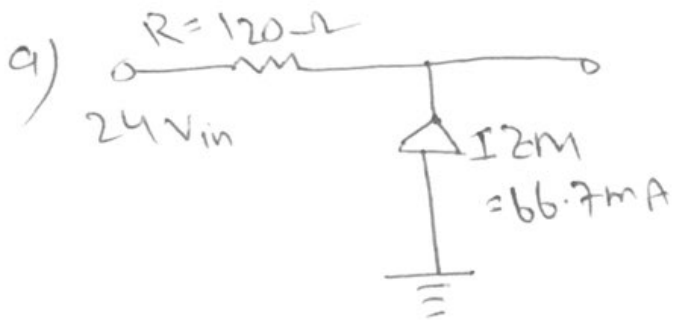
$$R = \frac{V_{IN} - V_{out}}{I_{ZM}}$$

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$$= \frac{24V - 16.1924V}{I_{ZM}} = \frac{7.8076}{66.7mA}$$

$$= 116.5313$$

$$R = 120\Omega$$



Part c

for the minimum level resistance
(maximum load current) the Zener
current is ($I_{ZK} = 0.25 \text{ mA}$)

$$I_T = \frac{V_{in} - V_{out}}{R} = \frac{24 - 14.7305}{120 \Omega}$$

$$I_T = 0.077245$$

$$I_T = 77.245 \text{ mA}$$

$$I_L = I_T - I_{ZK}$$

$$= 77.245 - 0.25 \text{ mA}$$

$$I_L = 76.995 \text{ mA}$$

$$R_L(\text{min}) = \frac{V_{out}}{I_L} = \frac{14.7305}{76.995 \text{ mA}} = \frac{14.7305}{0.076995}$$

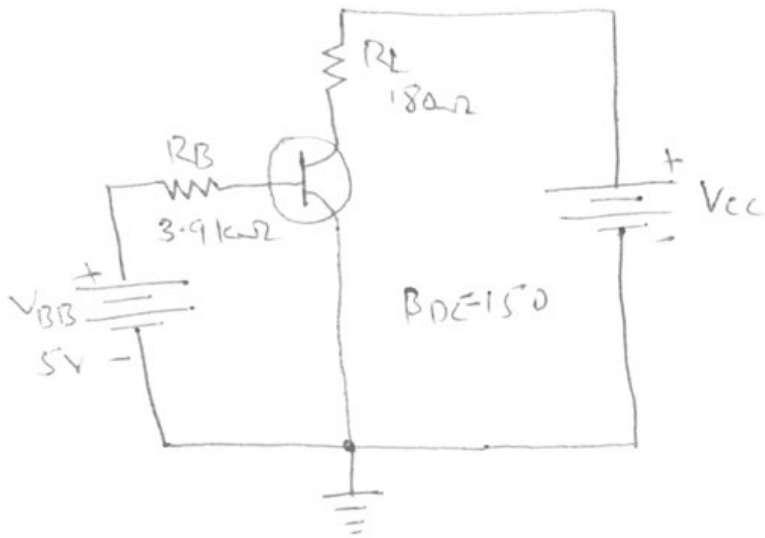
$$= 191.317618 \Omega$$

$$R_L(\text{min}) = 192 \Omega$$

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Q28 - Determine I_B , I_C , I_E , V_{BE} , V_{CE} and V_{CB}

~~Ans~~ V_{BE} in the circuit shown in fig 2



Solve

$$\Rightarrow V_{BE} = 0.7 \text{ V}$$

$$\Rightarrow I_B = \frac{V_{BB} - V_{BE}}{R_B} = \frac{5 \text{ V} - 0.7 \text{ V}}{3.9 \text{ k}\Omega} = \boxed{110.2 \mu\text{A}}$$

$$\Rightarrow I_C = \beta_{DC} \cdot I_B = (150) (110.2 \mu\text{A}) = \boxed{16.53 \text{ mA}}$$

$$\Rightarrow I_E = I_C + I_B = 16.53 \text{ mA} + 110.2 \mu\text{A} = \boxed{16.64 \text{ mA}}$$

Solve for V_{CE} & V_{CB}

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$$V_{CE} = V_{CC} - I_C R_C = 15V - (165.3mA)(180\Omega)$$
$$= 15V - 29.7V = \boxed{-14.7V}$$

$$V_{CB} = V_{CE} - V_{BE} \Rightarrow -14.7V - 0.7V$$
$$= \boxed{-15.4V}$$

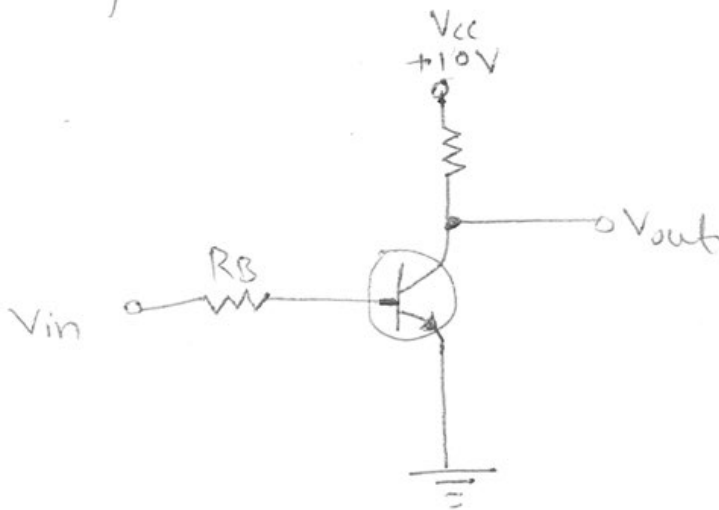
Since the collector is at a lower voltage than the base, the collector-base junction is forward biased.

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Q6:- For the transistor circuit given in Fig 3 calculate the following.

(a) what is V_{CE} when $V_{in} = 0V$?

(b) Determine the minimum value of I_B is required to saturate this transistor if β_{DC} is 125 and $V_{CE(sat)}$ is 0.4V.



Solution:-

Part (a):-

$$V_{CE} = ? \quad V_{in} = 0V$$

When $V_{in} = 0V$, so transistor is in cut off mode and $V_{CE} = V_{CC} = 10V$.

part (B)

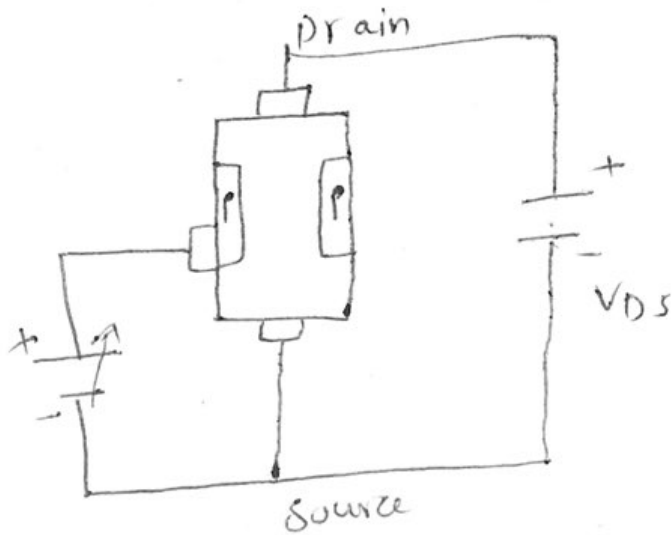
$$\text{min } I_B = ? \quad \beta_C = 125, \quad V_{CE} = 0.4$$

$$I_C(\text{sat}) = \frac{V_{CC}}{R_C} = \frac{10V}{1K\Omega} = 10mA$$

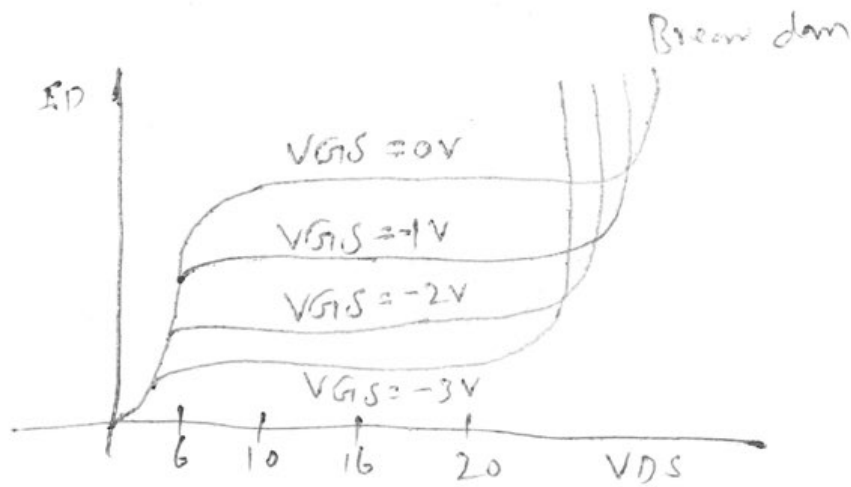
$$I_B(\text{min}) = \frac{I_C(\text{sat})}{\beta_{DC}} = \frac{10mA}{125} = \boxed{80\mu A}$$

Q5

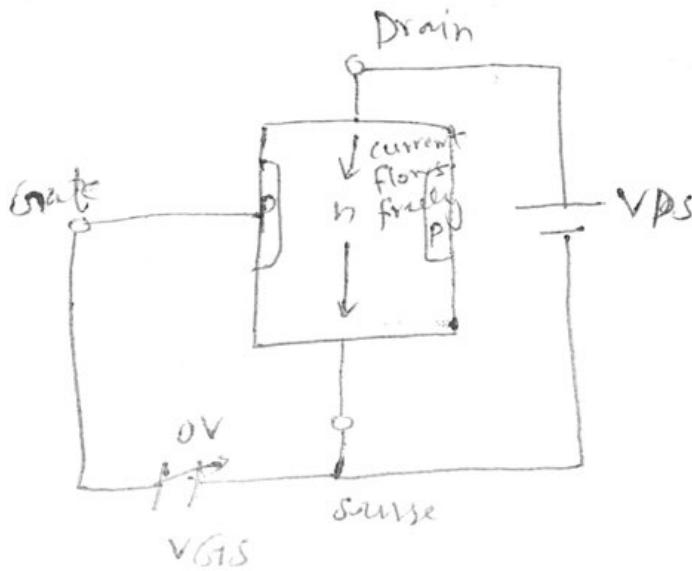
JFET is a type of junction field effect transistor which is voltage controlled device as differ from BJT which is current controlled



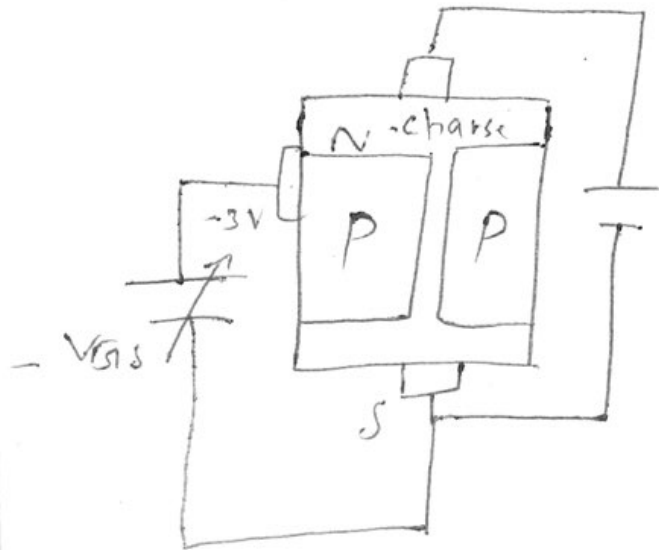
Actually in FET the drain to source current is controlled by the width of the channel the electric field is produced by the gate to source voltage.



So if we see to the graph
 with the no voltage applied
 to the gate the current flows
 freely



the channel are wider and
 Drain current moves freely
 if we move V_{GS} to
 negative value the channel
 width start to decrease
 and current cannot
 move.



So V_{GS} is more negative
So no current flows and

~~off~~ This effect is called Pinch
off region no current or
less current flows.

Q38-

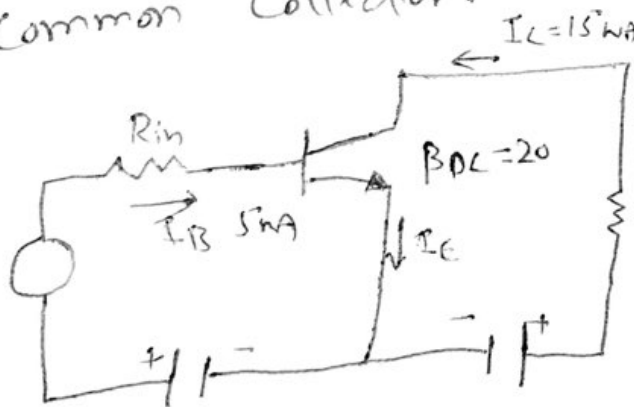
for using BJT as an amplifier we need to set them in Active region ~~become~~ because BJT working as an amplifier when use is active region.

Transistor has three Basic Configuration for using it in Amplification mode.

Common Base : voltage gain Current

Common Emitter: Both gain

Common Collector: Current gain no voltage.



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$$I_C = \beta \cdot I_B$$

$$= 200 + 5 \mu A$$

$$I_C = 200.00005 \mu A$$

$$I_E = I_C + I_B$$

$$I_E = 200.00005 \mu A + 15 \mu A$$

$$I_E = 200.00002$$